

CLAIM AMENDMENTS

1. (Currently Amended) A method for manufacturing a buried wiring structure comprising ~~the steps of:~~:
- forming a first depressed portion ~~on~~ in an insulating film;
- applying a burying material ~~on~~ said to the first depressed portion and ~~on~~ said insulating film ~~to bury said, filling the~~ first depressed portion;
- performing chemical mechanical polishing ~~of~~ said the burying material until the insulating film is exposed, ~~thereby~~ leaving the burying material in said the first depressed portion;
- forming a resist having a pattern of a second depressed portion that overlaps ~~said the~~ first depressed portion on said the insulating film ~~wherein said where the burying material has been buried is present;~~
- etching ~~said the~~ burying material and said the insulating film ~~to a predetermined depth,~~ using the resist as a mask, to form the second depressed portion;
- removing ~~said the~~ resist and said the burying material left after the ~~step of~~ etching; and
- depositing ~~a~~ an electrically conductive material in said the first depressed portion and said the second depressed portion.

2. (Currently Amended) A method for manufacturing a buried wiring structure comprising ~~the steps of:~~:
- depositing an insulating film on under-layer wiring;
- forming a contact hole in said the insulating film;
- applying a burying material ~~on~~ said to the contact hole and said the insulating film ~~to bury said, filling the~~ contact hole;
- performing chemical mechanical polishing ~~of~~ said the burying material until the insulating film is exposed, ~~thereby~~ leaving the burying material in said the contact hole;
- forming a resist having a pattern of a wiring channel that overlaps ~~said the~~ contact hole on said the insulating film ~~wherein said where the burying material has been buried is present;~~
- etching ~~said the~~ burying material and said the insulating film ~~to a predetermined depth,~~ using the resist as a mask, to form the wiring channel;
- removing ~~said the~~ resist and said the burying material left after the ~~step of~~ etching; and
- depositing ~~a~~ an electrically conductive material in said the contact hole and said the wiring channel.

3. (Currently Amended) A method for manufacturing a buried wiring structure comprising ~~the steps of:~~

depositing an insulating film on under-layer wiring;
forming a wiring channel in ~~said the~~ insulating film;
applying a burying material ~~on said to the~~ wiring channel and ~~said the~~ insulating film ~~to bury said, filling the~~ wiring channel;
~~performing~~ chemical mechanical polishing of ~~said the~~ burying material until the insulating film is exposed, ~~thereby~~ leaving the burying material in ~~said the~~ wiring channel;
forming a resist having a pattern of a contact hole that overlaps ~~said the~~ wiring channel on ~~said the~~ insulating film ~~wherein said where the~~ burying material ~~has been buried is present;~~
etching ~~said the~~ burying material and ~~said the~~ insulating film, using the resist as a mask, to form the contact hole;
removing ~~said the~~ resist and ~~said the~~ burying material left after the ~~step of~~ etching;
and
depositing ~~a~~ an electrically conductive material in ~~said the~~ contact hole and ~~said the~~ wiring channel.

4. (Currently Amended) The method for manufacturing a buried wiring structure according to claim 2, ~~wherein including applying as the~~ burying material an organic polymeric material having substantially the same etching rate as the ~~etching rate of~~ ~~said~~ insulating film ~~is used as said~~ burying material.

5. (Currently Amended) The method for manufacturing buried wiring structure according to claim 1, ~~wherein including applying as the~~ burying material an organic polymeric material containing no aromatic compounds ~~is used as said~~ burying material.

6. (Currently Amended) The method for manufacturing a buried wiring structure according to claim 5, further comprising ~~a step for~~ forming an antireflective film on ~~said the~~ insulating film ~~prior to the step of before~~ forming ~~said the~~ resist.

7. (Currently Amended) The method for manufacturing a buried wiring structure according to claim 6, wherein ~~said the~~ burying material and ~~said the~~ antireflective film are not soluble ~~to~~ in each other.